

MICROWAVE MIXER DIODE

DESCRIPTION:

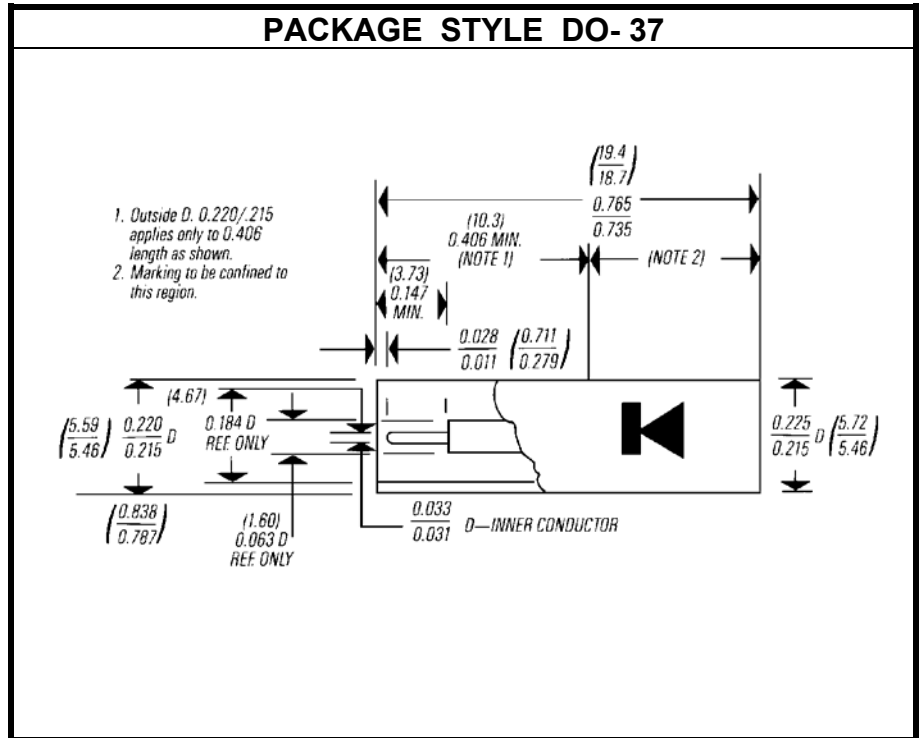
The **ASI BAT51E** is a Silicon Microwave Mixer Diode Designed for low noise performance in Applications Operating from 12 to 18 GHz.

FEATURES:

- Low Noise Figure
- Available in reverse polarity by adding suffix R
- Available in forward matched pairs by adding suffix MR
- Available in reverse matched pairs by adding suffix RM

MAXIMUM RATINGS

T_{AMB}	-55 °C to +100 °C
T_{STG}	-55 °C to +100 °C


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
I_R	$V_R = 0.5\text{ V}$			2.0	μA
I_F	$V_F = 0.5\text{ V}$	2.0			mA
N_O	$N_{IF} = 100\ \Omega$ $f = 13.5\text{ GHz}$		7.0		dB
L_C			5.2		dB
Z_{IF}		250	350	450	Ω